EDTM 2017: Poster Presentation

Poster Set-up: 9:00-12:00, Wednesday, March 1
Presentation Date & Time: 1) 18:25-19:05, Wednesday, March 1
2) 13:00-14:20, Thursday, March 2
* Poster presenters are requested to make presentations for both 1) and 2).
Poster Removal: 14:20-16:15, Thursday March 2
Room: Foyer (3F)

as of February 17, 2017

Poster No.	Ref. No	Name	Presenting Title	Affiliation	Country
P-1	0020	William Joseph Scheideler	UV-Annealing-Enhanced Stability in High-Performance Printed InO_x Transistors	University of California, Berkeley	United States
P-2	0038	Zuo Li	Random-Telegraph-Noise by Resonant Tunnelling at Low Temperatures	University of Southampton	United Kingdom
P-3	0048	Chitrakant Sahu	Fabrication of E-Mode InGaN/AlGaN/GaN HEMT Using FIB Based Lithography	Malaviya National Institute of Technology Jaipur	India
P-4	0060	Qing Luo	Endurance Characterization of the Cu-Dope HfO_2 Based Selection Device with One Transistor-One Selector Structure	Chinese Academy of Sciences	China
P-5	0063	Lei Liu	Investigation on Direct-Gap GeSn Alloys for High-Performance Tunneling Field-Effect Transistor Applications	Tsinghua University	China
P-6	0064	Peng Yao	Online Training on RRAM Based Neuromorphic Network: Experimental Demonstration and Operation Scheme Optimization	Tsinghua University	China
P-7	0069	Shan Wang	Uniformity Improvements of Low Current 1T1R RRAM Arrays through Optimized Verification Strategy	Tsinghua University	China
P-8	0098	Fumihiro Hattori	Electroluminescence Characteristics of Rare Earth Doped Silicon Based Light Emitting Device	Toyama Prefectural University	Japan
P-9	0101	Ming-Hao Kuo	High Photoresponsivity Germanium Nanodot PhotoMOSFETs for Monolithically-Integrated Si Optical Interconnects	National Central University	Taiwan
P-10	0108	Andrew Marshall	The Impact of Oxygen Insertion Technology on SRAM Yield Performance	The University of Texas at Dallas	United States
P-11	0111	Fayong Liu	Transport Properties in Silicon Nanowire Transistors with Atomically Flat Interfaces	University of Southampton	United Kingdom
P-12	0129	Eiji Kume	InAs MOS-HEMT Power Detector for 1.0 THz on Quartz Glass	IRspec Corporation	Japan
P-13	0140	Chetan Gupta	Analysis and Modeling of Capacitances in Halo-Implanted MOSFETs	Indian Institute of Technology, Kanpur	India
P-14	0144	Tsuyoshi Kondo	Design and Performance of Thin-Film μTEG Modules for Wearable Device Applications	Tokyo Institute of Technology	Japan
P-15	0147	Taiju Akushichi	Analysis of Spin Accumulation in a Si Channel Using CoFe/MgO/Si Spin Injectors	Tokyo Institute of Technology	Japan
P-16	0149	Krishna Mohan Chavali	SER Scaling and Trends in Planar Submicron Technology Nodes	GLOBALFOUNDRIES Inc.	United States
P-17	0035	Galo Andres Torres Sevilla	Fully Packaged Compliant CMOS Electronic Systems for IoT and IoE Applications	King Abdulla University of Science and Technology	Saudi Arabia
P-18	0100	Jiebin Gu	A Metal Micro-Casting Method for Through-Silicon Via (TSV) Fabrication	Shanghai Institute of Microsystem And Information Technology	China
P-19	0014	Guo-Hua Feng	Acoustic Emission Wave Sensor with Thermally Controllable Force-Enhancement Mechanism for Acoustic Emission Source Detection and Biomedical Application	National Chung Cheng University	Taiwan
P-20	0019	Guo-Hua Feng	Electroactive Polymer Actuated Gripper Enhanced with Iron Oxide Nanoparticles and Water Supply Mechanism for Millimeter-Sized Fish Roe Manipulation	National Chung Cheng University	Taiwan
P-21	0043	Shiro Satoh	Low Temperature Hermetic Sealing by Aluminum Thermocompression Bonding Using Tin Intermediate Layer	Tohoku University	Japan
P-22	0110	Jun'ichi Shimizu	Low-Carrier Density Sputtered-MoS_2 film by H_2S Annealing for Normally-Off Accumulation-Mode FET	Tokyo Institute of Technology	Japan
P-23	0119	Chia-Chi Fan	Impact of Ferroelectric Domain Switching in Nonvolatile Charge-Trapping Memory	National Chiao Tung University	Taiwan
P-24	0121	Norio Umeyama	An In-Line MOSFET Process with Photomask Fabrication Process in a Minimal Fab	National Institute of Advanced Industrial Science and Technology (AIST)	Japan

Poster No.	Ref. No	Name	Presenting Title	Affiliation	Country
P-25	0123	Norio Umeyama	Development of a Half-Inch Wafer for Minimal Fab Process	National Institute of Advanced Industrial Science and Technology (AIST)	Japan
P-26	0141	Shinichi Ogawa	Helium Ion Microscopy (HIM) for Imaging Fine Line Features Patterned Organic Film with Less Damage	National Institute of Advanced Industrial Science and Technology (AIST)	Japan
P-27	0142	Yu Zhao	Supercritical Fluid Deposition of Conformal Oxide Films: 3-Dimentionally-Stacked $RuO_2/TiO_2/RuO_2$ Structures for MIM Capacitors	The University of Tokyo	Japan
P-28	0146	Shin Hirano	Crystallinity Improvement Using Migration-Enhancement Methods for Sputtered-MoS_2 Film	Tokyo Institute of Technology	Japan
P-29	0037	Amitesh Kumar	Low Power Transparent Resistive Switching Device with Memristive Behavior	Indian Institute of Technology Indore	India
P-30	0055	Makiko Irie	Photoresist Development for Wafer-Level Packaging Process	Tokyo Ohka Kogyo Co.,ltd	Japan
P-31	0075	Kangwei Wang	Second-Harmonic Susceptibility Enhancement in Gallium Nitride Nanopillars	University of California, San Diego	United States
P-32	0078	Kenta Chokawa	Defect Formation in SiO_2 Formed by Thermal Oxidation of SiC	Nagoya University	Japan
P-33	0115	Hiroyasu Ichikawa	Current Enhanced Solid Phase Precipitation (CE-SPP) for Direct Deposition of Multilayer Graphene on SiO_2 from a Cu Capped Co-C Layer	Shibaura Institute of Technology	Japan
P-34	0118	Libin Liu	Enhanced Photoresponse of InGaZnO TFT to Ultraviolet Illumination by Using a High-*k* Dielectric	Tsinghua University	China
P-35	0124	Jihee Jeon	Development of *in-situ* Sb-Doped $Ge_{1-x}Sn_x$ Epitaxial Layers for Source/Drain Stressor of Strained Ge Transistors	Nagoya University	Japan
P-36	0126	Keisuke Kawamoto	Novel In-situ Passivation of $MoCl_5$ Doped Multilayer Graphene with MoO_x for Low-Resistance Interconnects	Shibaura Institute of Technology	Japan
P-37	0143	Shinji Migita	Thickness-Independent Behavior of Coercive Field in HfO_2-Based Ferroelectrics	National Institute of Advanced Industrial Science and Technology (AIST)	Japan
P-38	0152	Wenchang Yeh	Crystallinity Study of Si Single Crystal Stripe on Bended Glass Substrate Fabricated by Micro-Chevron Laser Beam Scanning Method	Shimane University	Japan
P-39	0011	T. K. Maiti	Physics Based System Simulation for Robot Electro-Mechanical Control Design	Hiroshima University	Japan
P-40	0046	Lei Chen	Accurate Modeling of MOSFET Aging Based on Trap-Density Increase for Predicting Circuit-Performance Aging	Hiroshima University	Japan
P-41	0070	Runtao Ning	Modeling and Analysis of Depletion-Mode NMOS Transistor as Transmitter/Receiver RF Switch	Illinois Institute of Technology	United States
P-42	0071	Renrong Liang	An Analytical Charge-Sheet Drain Current Model for Monolayer Transition Metal Dichalcogenide Negative Capacitance Field-effect Transistors	Tsinghua University	China
P-43	0130	Naoki Azuma	A Simple Test Method for Electromigration Reliability of Solder/Cu Pillar Bumps Using Flat Cables	Shibaura Institute of Technology	Japan